

ACJT610-10H

Peak pulse voltage
($T_j=25$; non-repetitive, off-state)

Symbol	Test Condition			
I_{GT}	$V_D=12V R_L=33$			
V_{GT}				
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$			
I_L	$I_G=1.2I_{GT}$	MAX.	35	mA
I_H	$I_T=100mA$	MAX.	20	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$	MIN.	300	V/ μs
(dI/dt) _c	(dV/dt) _c =10V/ μs , $T_j=125$	MIN.	3	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$	TYP.		

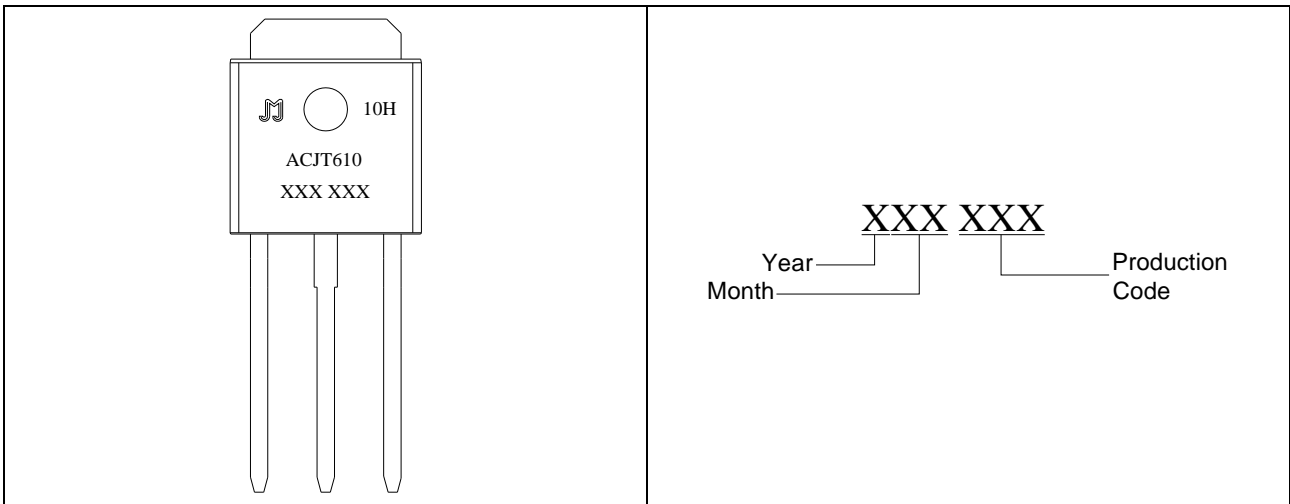
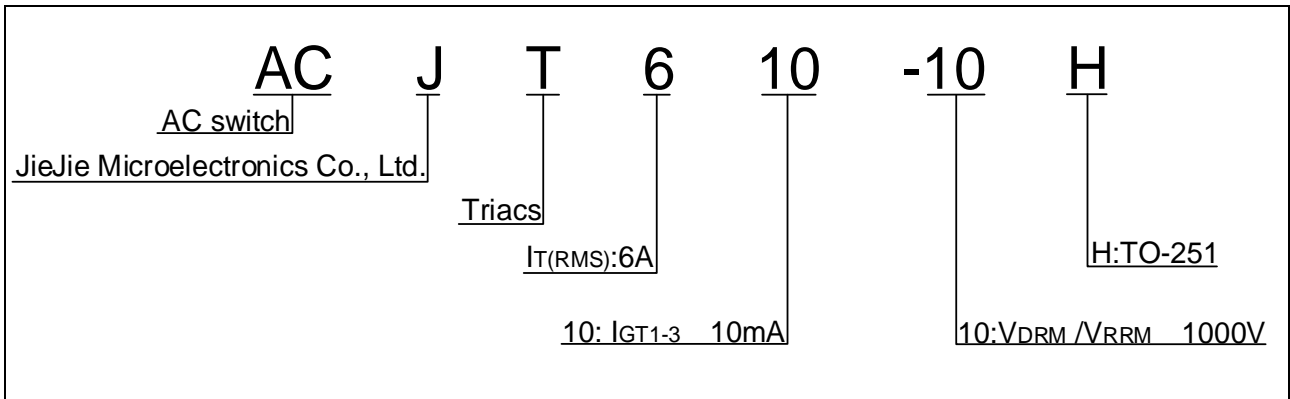


FIG.1: Maximum power dissipation versus RMS on-state current

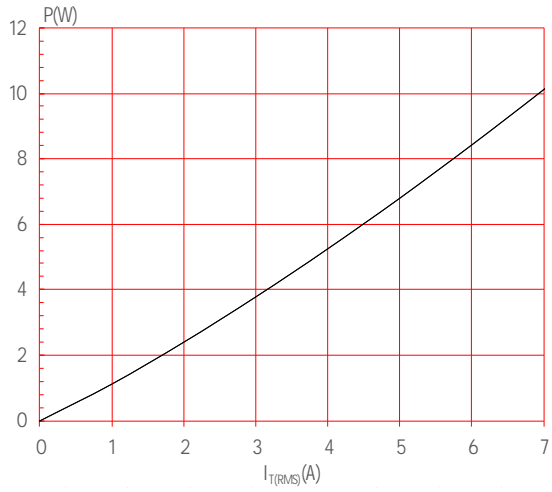


FIG.3: Surge peak on-state current versus number of cycles

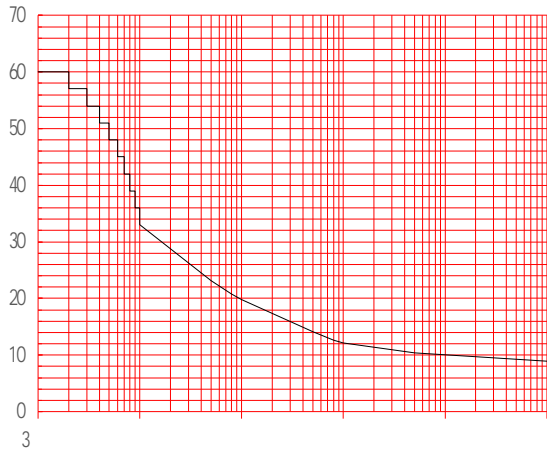


FIG.2: RMS on-state current versus case temperature

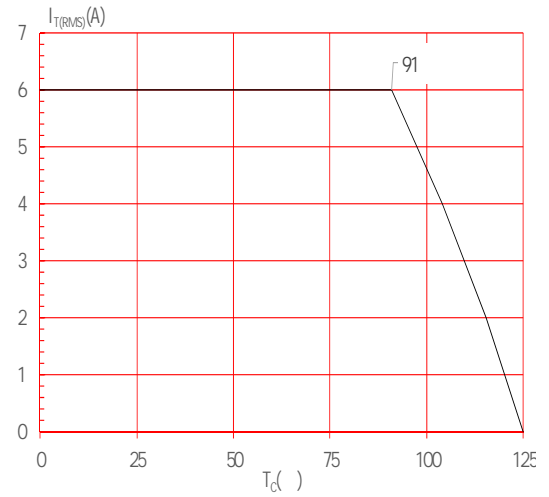
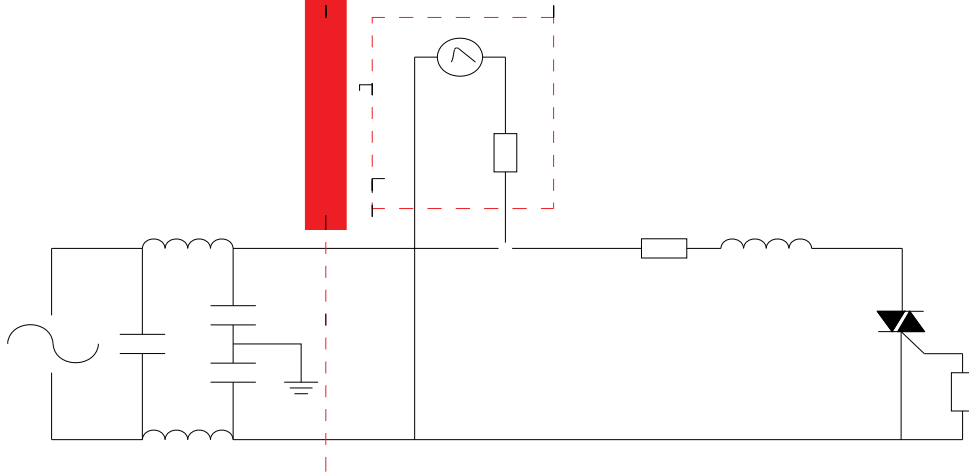
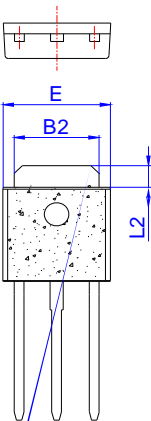


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards




Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery
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